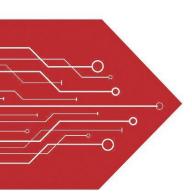
# MSKSEMI















**ESD** 

**TVS** 

**TSS** 

MOV

**GDT** 

**PLED** 

Broduct data speet



#### **Features**

- Ultra low leakage: nA level
- Operating voltage: 5.0V
- Low clamping voltage
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV

Contact discharge: ±25kV

- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (EFT) 5A (8/20ns)

**RoHS Compliant** 

# **Applications**

- USB 2.0 power and data line
- Set-top box and digital TV
- Digital video interface (DVI)
- **Notebook Computers**
- SIM Ports
- 10/100 Ethernet

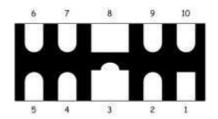
# **Mechanical Characteristics**

Package: DFN2510P10

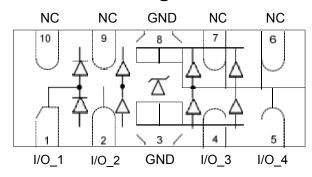
Lead Finish: Lead Free

- UL Flammability Classification Rating 94V-0
- Quantity Per Reel:3,000pcs
- Reel Size:7 inch

#### **Dimensions DFN2510P10**

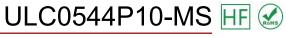


# **Pin Configuration**



# Absolute Maximum Ratings(Tamb=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ррр	150	W
ESD per IEC 61000-4-2 (Air)	V <sub>ESD</sub>	±15	Kv
ESD per IEC 61000-4-2 (Contact)	VESD	±8	- KV
Operating Temperature Range	TJ	-55 to +125	$^{\circ}$
Storage Temperature Range	T <sub>STJ</sub>	-55 to +150	$^{\circ}$ C







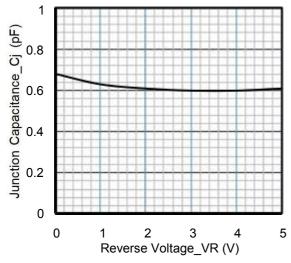
# Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	150	W
Peak Pulse Current (8/20μs)	<b>I</b> PP	5	А
ESD per IEC 61000-4-2 (Air)	VESD	±30	147
ESD per IEC 61000-4-2 (Contact)	VESD	±25	kV
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

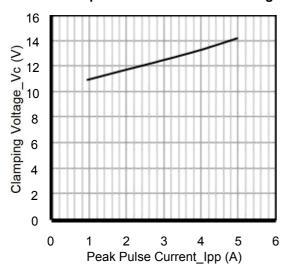
## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	Any I/O pin to ground
Breakdown Voltage	VBR	6			V	IT = 1mA, any I/O pin to ground
Reverse Leakage Current	I <sub>R</sub>			0.5	μA	VRWM = 5V, any I/O pin to ground
Clamping Voltage	Vc			15	V	IPP = 1A (8 x 20µs pulse), any I/O pin to ground
Clamping Voltage	Vc			20	V	IPP = 5A (8 x 20µs pulse), any I/O pin to ground
Junction Capacitance	C1		0.3	0.4	pF	VR = 0V, f = 1MHz, between I/O pins
Junction Capacitance	Cl			0.8	pF	VR = 0V, f = 1MHz, any I/O pin to ground

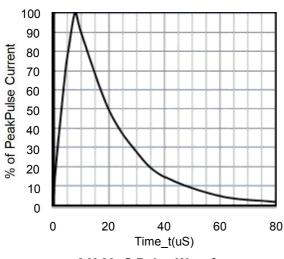
### Typical Performance Characteristics (T<sub>A</sub>=25°C unless otherwise Specified)



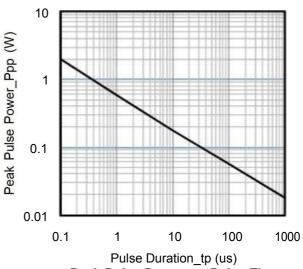
Junction Capacitance vs. Reverse Voltage



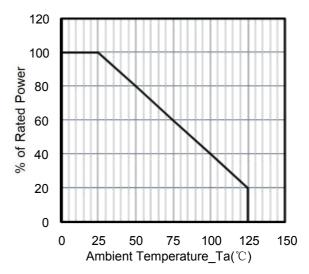
Clamping Voltage vs. Peak Pulse Current



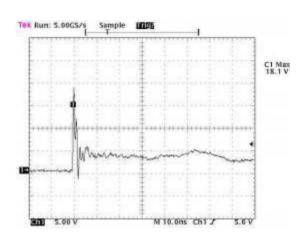
8 X 20uS Pulse Waveform



Peak Pulse Power vs. Pulse Time



**Power Derating Curve** 



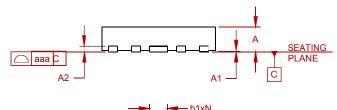
**ESD Clamping Voltage** 8 kV Contact per IEC61000-4-2

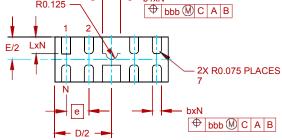


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#### **PACKAGE MECHANICAL DATA**



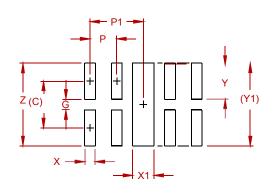


Dimensions in millimeters



DIMENSI ONS						
DIM	INCHES		MILLIN	MILLIMETERS		
J	MIN	NOM	MAX	MIN	NOM	MAX
Α	.020	.023	.026	0.50	0.58	0.65
A1	0.00	.001	.002	0.00	0.03	0.05
A2	(.005)			(0	).13)	
b	.006	.008	.010	0.15	0.20	0.25
b1	.014	.016	.018	0.35	0.40	0.45
D	.094	.098	.102	2.40	2.50	2.60
E	.035	.039	.043	0.90	1.00	1.10
е	.020 BSC		0.50	BSC		
L	.012	.015	.017	0.30	0.38	0.425
N	8		8			
aaa	.003		0.08			
bbb	.004			0.10		

#### **Suggested Pad Layout**



DIMENSIONS			
DIM	INCHES	MILLIMETERS	
С	(.034)	(0.875)	
G	.008	0.20	
Р	.020	0.50	
P1	.039	1.00	
Х	.008	0.20	
X1	.016	0.40	
Y	.027	0.675	
Y1	(.061)	(1.55)	
Z	.061	1.55	

#### NOTES:

CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES). THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
ULC0544P10-MS	DFN2510P10	3000



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